Onsemi

Silicon Carbide (SiC) **Schottky Diode** – EliteSiC, 30 A, 650 V, D1, TO-247-2L

FFSH3065A

Description

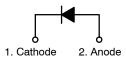
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 180 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- This Device is Pb-Free and is RoHS Compliant

Applications

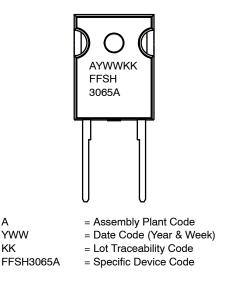
- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



Schottky Diode



MARKING DIAGRAM



ORDERING INFORMATION

A

See detailed ordering and shipping information on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise specified)

Symbol	Parameter		FFSH3065A	Unit
V _{RRM}	Peak Repetitive Reverse Voltage	650	V	
E _{AS}	Single Pulse Avalanche Energy (Note 1)	Ilse Avalanche Energy (Note 1)		
١ _F	Continuous Rectified Forward Current	@ Tc < 145°C	30	A
		@ Tc < 135°C	36	
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	Tc = 25°C, 10 μs	1125	A
		Tc = 150°C, 10 μs	1040	A
I _{F, SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	150	A
I _{F, RM}	Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	75	A
P _{tot}	Power Dissipation	Tc = 25°C	259	W
		Tc = 150°C	43	W
T _J , T _{STG}	Operating and Storage Temperature Range		–55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. E_{AS} of 180 mJ is based on starting $T_J = 25^{\circ}C$, L = 0.5 mH, $I_{AS} = 27$ A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Rating	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.58	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter Test Conditions		Min	Тур	Max	Unit
V _F	Forward Voltage	IF = 30 A, Tc = 25°C	-	1.50	1.75	V
		I⊧ = 30 A, Tc = 125°C	-	1.60	2.0	
		IF = 30 A, Tc = 175°C	-	1.72	2.4	
I _R	Reverse Current	VR = 650 V, Tc = 25°C	-	-	200	μA
		VR = 650 V, Tc = 125°C	-	-	400	
		VR = 650 V, Tc = 175°C	-	-	600	
Q _C	Total Capacitive Charge	V = 400 V	-	100	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	1705	-	pF
		V _R = 200 V, f = 100 kHz	-	180	-	
		V _R = 400 V, f = 100 kHz	_	130	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSH3065A	FFSH3065A	TO-247-2L	Tube	N/A	N/A	30 Units

TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

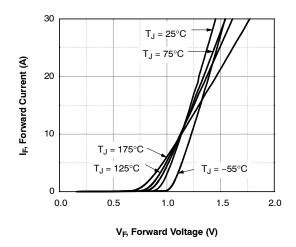
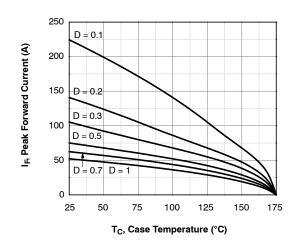
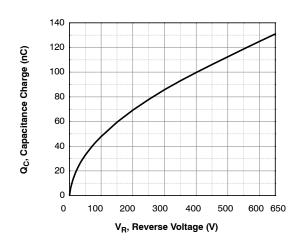


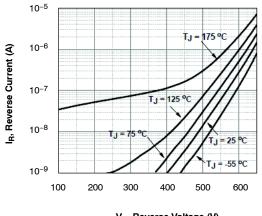
Figure 1. Forward Characteristics











V_R, Reverse Voltage (V)

Figure 2. Reverse Characteristics

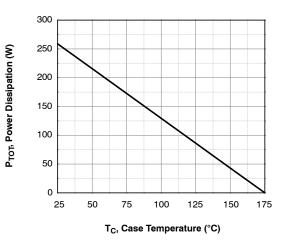


Figure 4. Power Derating

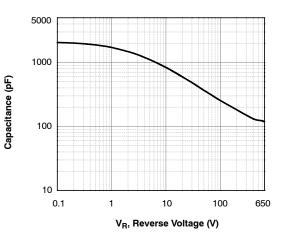
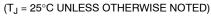
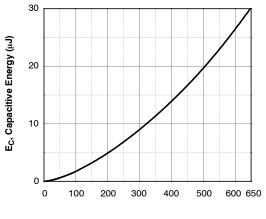


Figure 6. Capacitance vs. Reverse Voltage





V_R, Reverse Voltage (V)



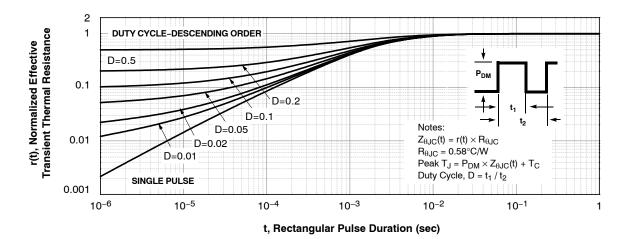


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

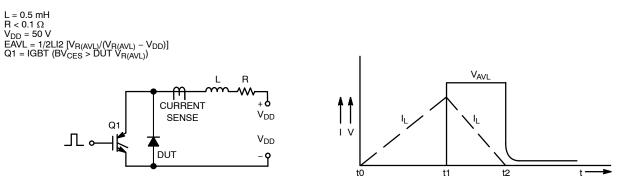


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

1

MILLIMETERS

NOM

4.70

2.40

1.50

1.26

1.65

0.61

20.57

16.57

0.93

15.62

~

5.08

11.12

16.00

3.81

3.58

6.73

5.46

5.46

MAX

4.82

2.66

1.70

1.35

1.77

0.71

20.82

16.77

1.35

15.87

~

5.20

~

16.25

3.93

3.65

6.85

5.58

5.58

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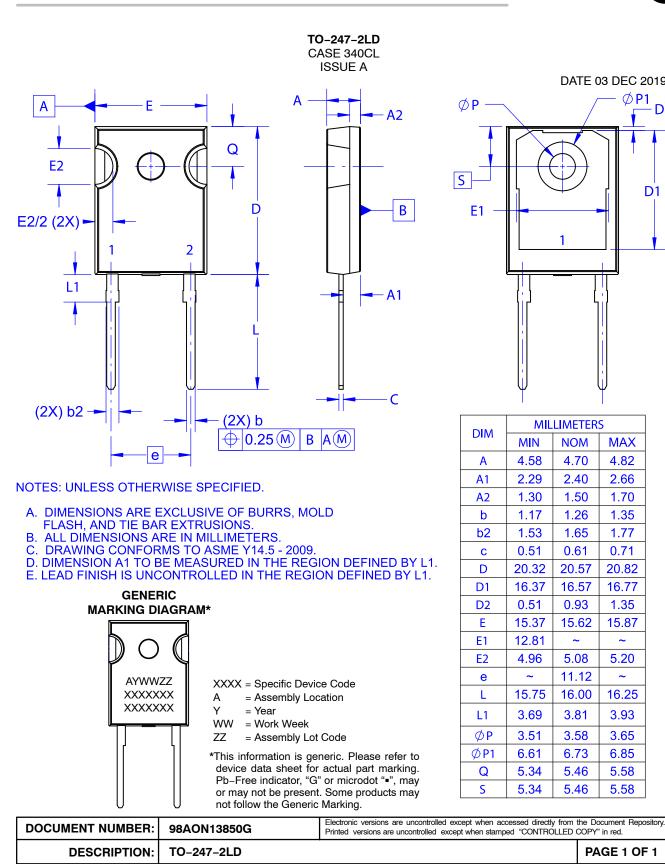
DATE 03 DEC 2019

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D2

D1



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